

SANYO

No.1881A

DRA03T

Silicon Planar Type

0.3A Reverse Blocking Thyristor**Features**

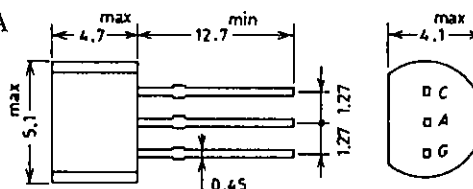
- Low-power switching and control
- Small size and light weight
- Peak OFF-state (reverse) voltage : -100 to -600V
- Average ON-state current : 0.3A
- TO92 package

Absolute Maximum Ratings at Ta = 25°C

			DRA03TB	DRA03TC	DRA03TE	DRA03TG	unit
Repetitive Peak OFF-State Voltage	V_{DRM}	$R_{GK} = 1\Omega$	100	200	400	600	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}	$R_{GK} = 1\Omega$	-150	-300	-500	-720	V
Repetitive Peak Reverse Voltage	V_{RRM}	$R_{GK} = 1\Omega$	-100	-200	-400	-600	V
Average ON-State Current	$I_{T(AV)}$	Ta = 30°C, single-phase half-wave	→	→	→	0.3	A
RMS ON-State Current	$I_{T(RMS)}$		→	→	→	0.45	A
Surge ON-State Current	I_{TSM}	Sine half-wave 1 cycle, 50Hz	→	→	→	9	A
Amperes Squared-Seconds	$\int i^2 T \cdot dt$	1ms ≤ t ≤ 10ms	→	→	→	0.4	A ² S
Peak Gate Power Dissipation	P_{GM}	f ≥ 50Hz, duty ≤ 10%	→	→	→	0.1	W
Average Gate Power Dissipation	$P_{G(AV)}$		→	→	→	0.01	W
Peak Gate Forward Current	I_{FGM}	f ≥ 50Hz, duty ≤ 10%	→	→	→	0.125	A
Peak Gate Forward Voltage	V_{FGM}	f ≥ 50Hz, duty ≤ 10%	→	→	→	3.5	V
Peak Gate Reverse Voltage	V_{RGM}		→	→	→	-5	V
Junction Temperature	Tj		→	→	→	110	°C
Storage Temperature	Tstg		→	→	→	-40 to +125	°C
Weight			→	→	→	0.2	g

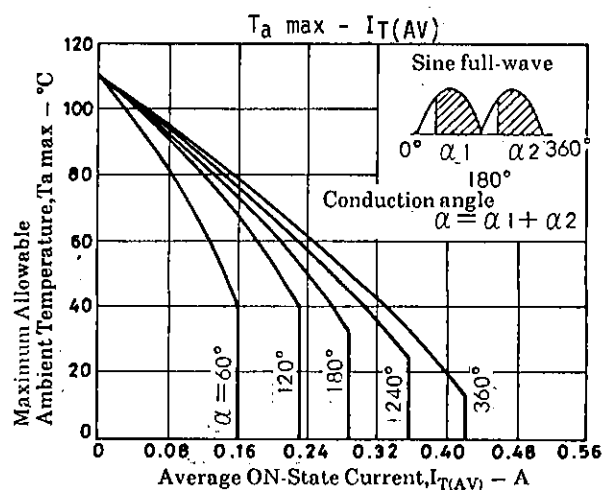
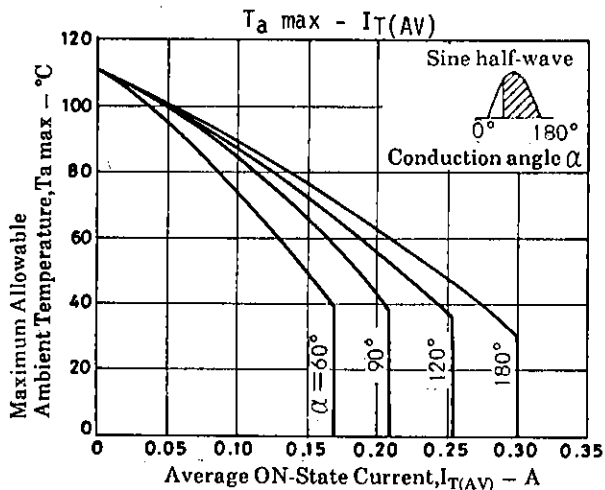
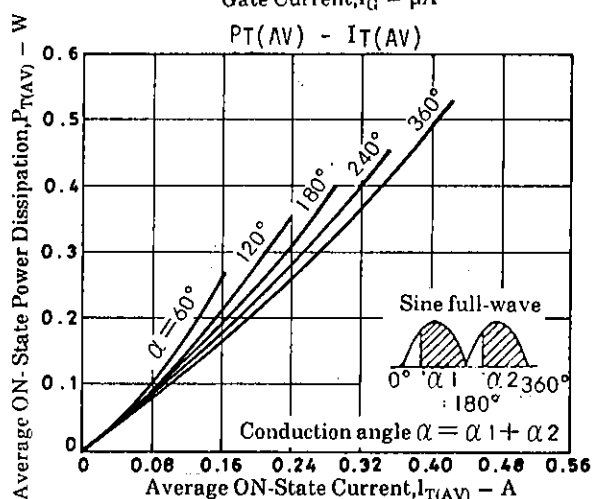
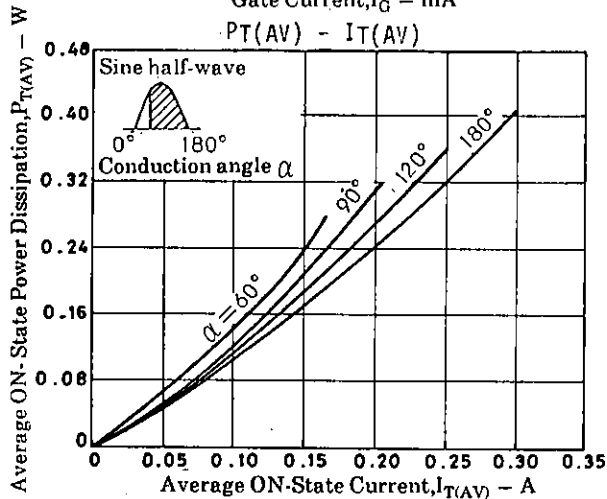
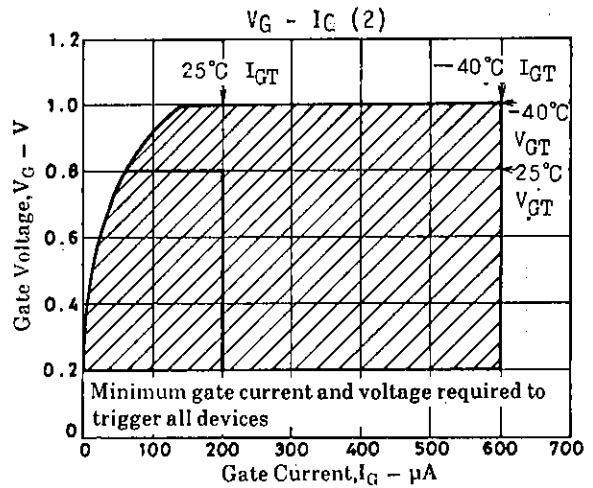
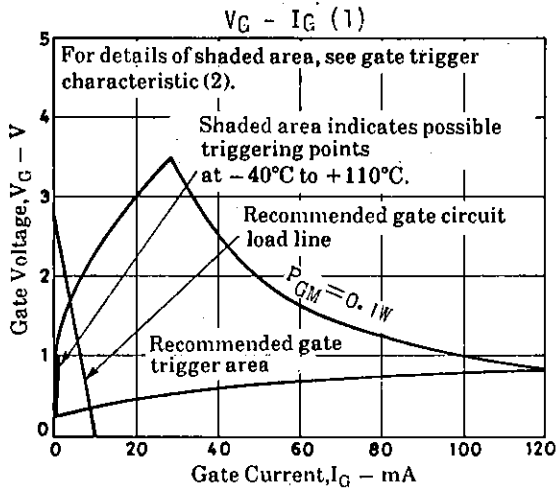
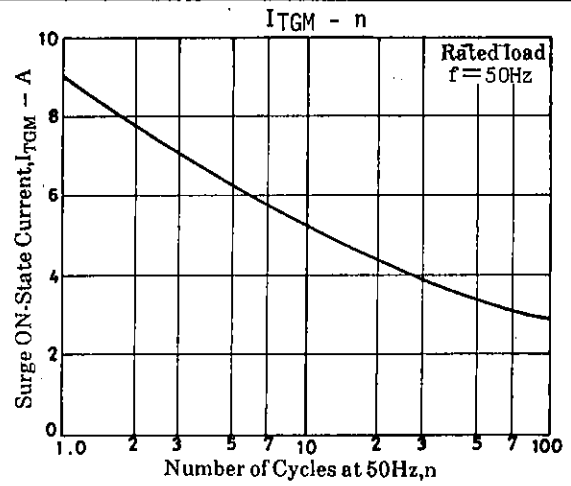
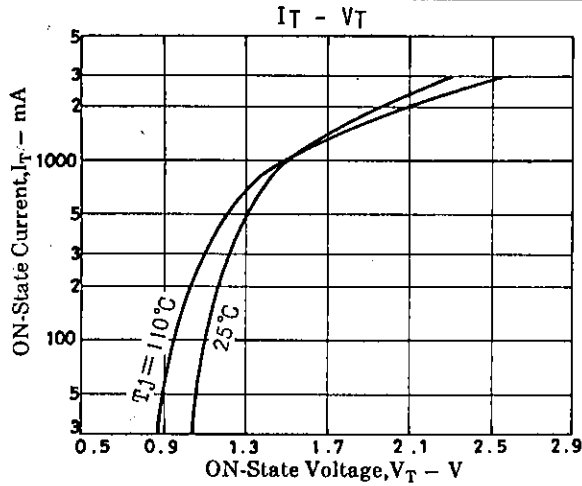
Electrical Characteristics at Ta = 25°C

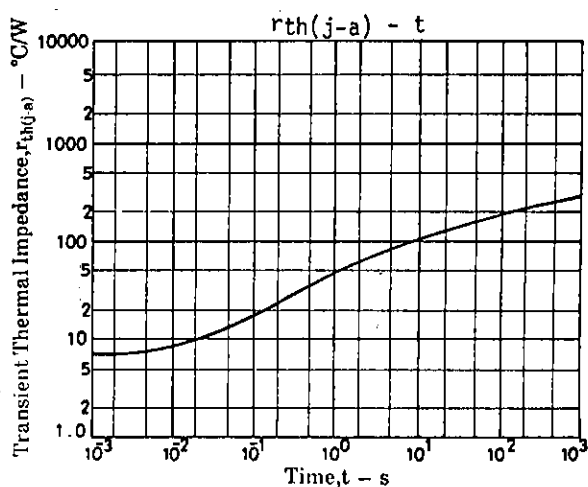
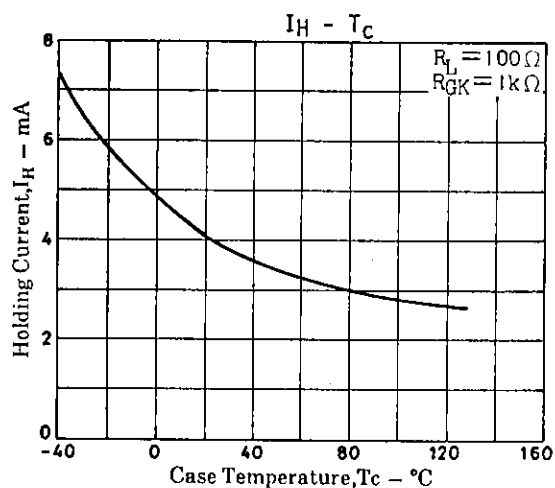
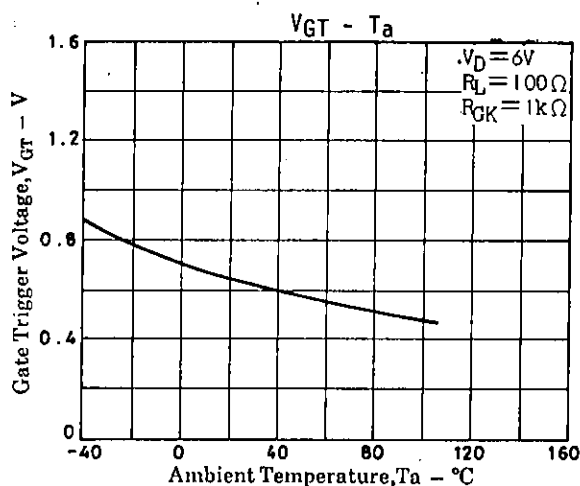
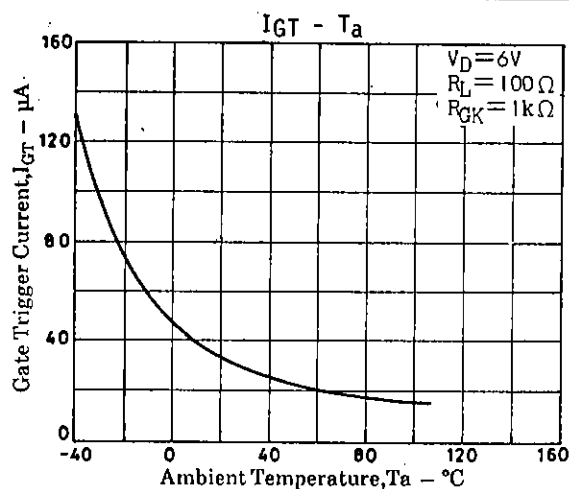
			min	typ	max	unit
Repetitive Peak OFF-State Current	I_{DRM}	Tj = 110°C, $V_D = V_{DRM}$, $R_{GK} = 1k\Omega$			0.1	mA
Repetitive Peak Reverse Current	I_{RRM}	Tj = 110°C, $V_D = V_{RRM}$, $R_{GK} = 1k\Omega$			0.1	mA
ON-State Voltage	V_T	$I_T = 2A$			2.0	V
Holding Current	I_H	$R_L = 100\Omega$, $R_{GK} = 1k\Omega$		4.0		mA
Gate Trigger Current	I_{GT}	$V_D = 6V$, $R_L = 100\Omega$, $R_{GK} = 1k\Omega$			0.2	mA
Gate Trigger Voltage	V_{GT}	$V_D = 6V$, $R_L = 100\Omega$, $R_{GK} = 1k\Omega$			0.8	V
Gate Nontrigger Voltage	V_{GD}	Ta = 110°C, $V_D = 6V$, $R_{GK} = 1k\Omega$	0.2			V
Thermal Resistance	$R_{th(j-c)}$				250	°C/W

Package Dimensions 1096A
(unit: mm)

C: Cathode
A: Anode
G: Gate

DRA03T





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